Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|-----------------------|----------------|---------|-----------|------------|----------|
| FQA11N90C | FQA11N90C | TO-3P | | | 30 |
| FQA11N90C | FQA11N90C_F109 | TO-3PN | | | 30 |

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units | | | |
|--------------------------------|--|--|-----|------|------|-------|--|--|--|
| Off Characteristics | | | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V_{GS} = 0 V, I_{D} = 250 μ A | 900 | | | V | | | |
| $\Delta BV_{DSS}/\Delta T_{J}$ | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | | 1.02 | | V/°C | | | |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 900 V, V _{GS} = 0 V | | | 10 | μА | | | |
| | | V _{DS} = 720 V, T _C = 125°C | | | 100 | μА | | | |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 30 V, V _{DS} = 0 V | | | 100 | nA | | | |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -30 V, V _{DS} = 0 V | | | -100 | nA | | | |
| On Charact | eristics | | • | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 3.0 | | 5.0 | V | | | |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10 V, I _D = 5.5 A | | 1.12 | 1.4 | Ω | | | |
| 9 _{FS} | Forward Transconductance | V _{DS} = 50 V, I _D = 5.5 A (Note 4) | | 9.0 | | S | | | |
| Dynamic Cl | naracteristics | | | | | | | | |
| C _{iss} | Input Capacitance | Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ | | 2530 | 3290 | pF | | | |
| C _{oss} | Output Capacitance | f = 1.0 MHz | | 215 | 280 | pF | | | |
| C _{rss} | Reverse Transfer Capacitance | - | | 23 | 30 | pF | | | |
| Switching C | Characteristics | | | | | | | | |
| t _{d(on)} | Turn-On Delay Time | | | 60 | 130 | ns | | | |
| t _r | Turn-On Rise Time | $R_{G} = 25 \Omega$ | | 130 | 270 | ns | | | |
| t _{d(off)} | Turn-Off Delay Time | Alata 4 5) | | 130 | 270 | ns | | | |
| t _f | Turn-Off Fall Time | (Note 4, 5) | | 85 | 180 | ns | | | |
| Qg | Total Gate Charge | V _{DS} = 720 V, I _D = 11.0A, | | 60 | 80 | nC | | | |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10 V | | 13 | | nC | | | |
| Q _{gd} | Gate-Drain Charge | (Note 4, 5) | | 25 | | nC | | | |
| Drain-Source | ce Diode Characteristics and Maximum Ratings | | | II. | II. | | | | |
| I _S | Maximum Continuous Drain-Source Diode Fo | | | 11.0 | Α | | | | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward | | | 44.0 | Α | | | | |
| V_{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S =11.0 A | | | 1.4 | V | | | |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 11.0 A, | | 1000 | | ns | | | |
| Q _{rr} | Reverse Recovery Charge | $dI_F / dt = 100 A/\mu s \qquad (Note 4)$ | | 17.0 | | μС | | | |

NOTES

^{1.} Repetitive Rating : Pulse width limited by maximum junction temperature

^{2.} L = 15mH, I $_{AS}$ =11.0A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C

^{3.} $I_{SD} \le$ 11.0A, di/dt \le 200A/ μ s, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C

^{4.} Pulse Test : Pulse width $\leq 300 \mu \text{s}, \, \text{Duty cycle} \leq 2\%$

^{5.} Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

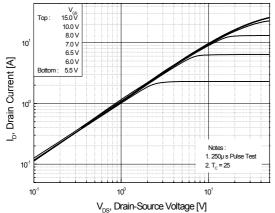


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

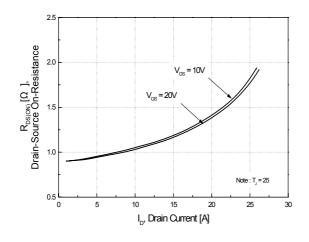


Figure 5. Capacitance Characteristics

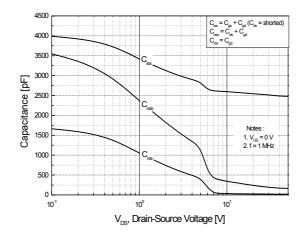


Figure 2. Transfer Characteristics

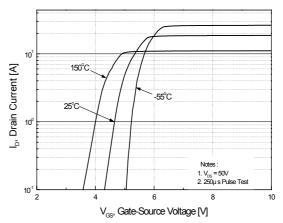


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

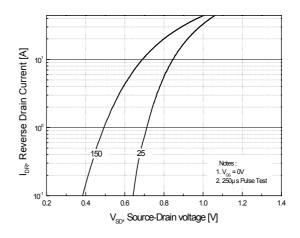
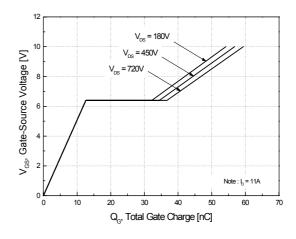


Figure 6. Gate Charge Characteristics



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Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

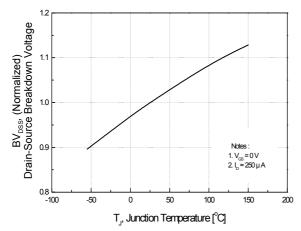


Figure 9. Maximum Safe Operating Area

Figure 8. On-Resistance Variation vs. Temperature

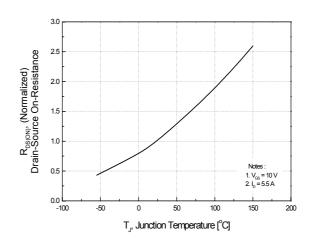


Figure 10. Maximum Drain Current vs. Case Temperature

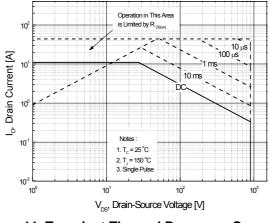
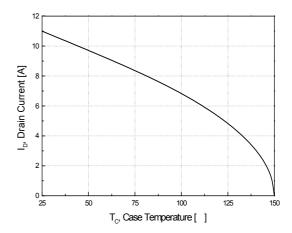
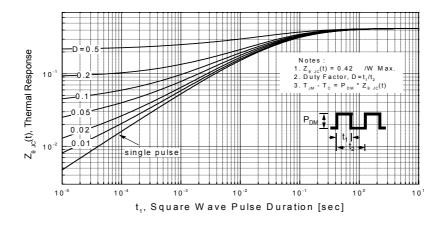


Figure 11. Transient Thermal Response Curve

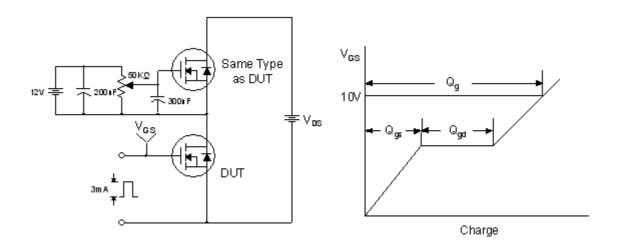




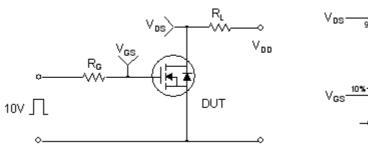
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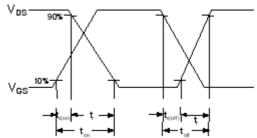
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Gate Charge Test Circuit & Waveform

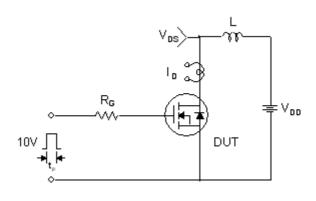


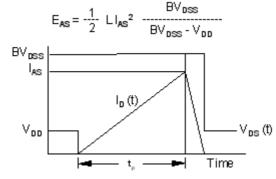
Resistive Switching Test Circuit & Waveforms



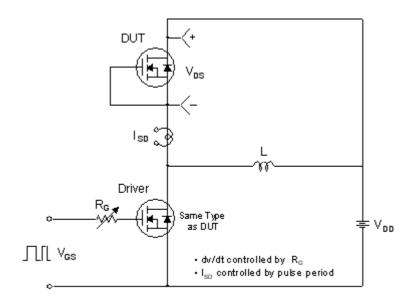


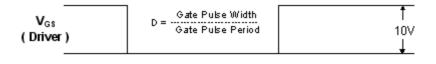
Unclamped Inductive Switching Test Circuit & Waveforms

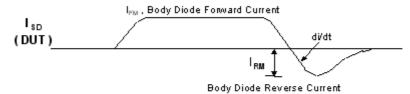


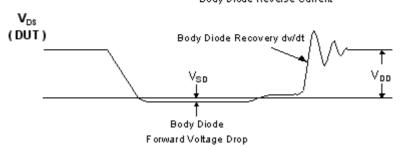


Peak Diode Recovery dv/dt Test Circuit & Waveforms



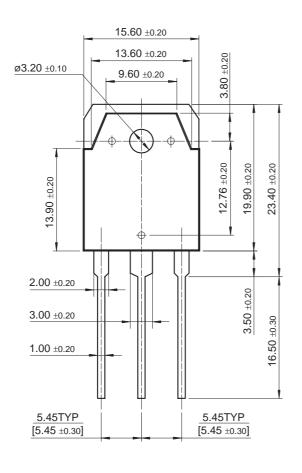


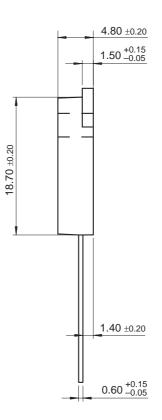




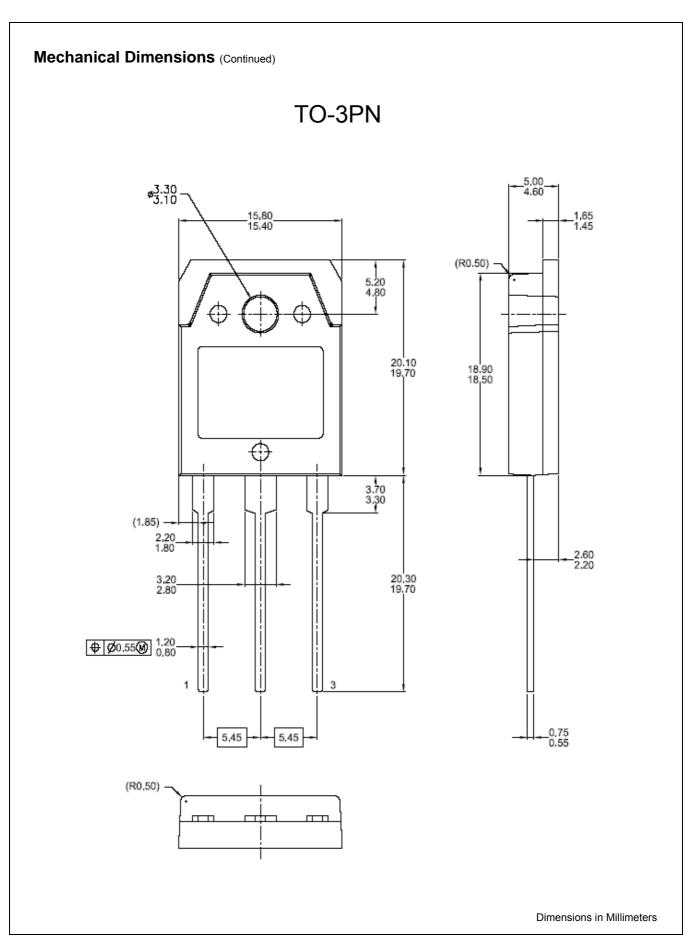
Mechanical Dimensions

TO-3P





Dimensions in Millimeters



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